# **EECS151: Introduction to Digital Design and ICs**

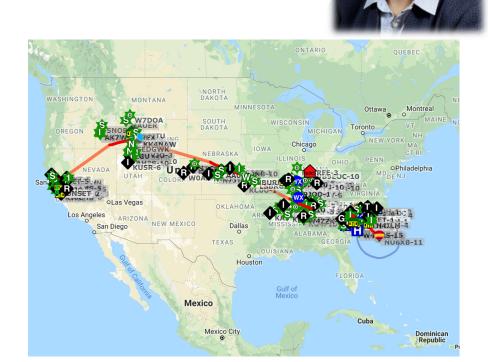
## Lecture 19 – Caches

# Bora Nikolić and Sophia Shao



Nov. 14, 2019. Students in EE-84 class taught by Prof. Miki Lustig launched a balloon equipped with a transponder and GPS+solar cells+super capacitors, can be tracked:

https://aprs.fi/#!mt=roadmap&z=8&call=a%2FNU6XB11&timerange=





#### Review

- Flip-flop is typically a latch pair
- Setup and hold times are defined at constant percentage increases over clk-q delay
- SRAM has unique combination of density, speed, power
- SRAM cells sized for stability and writeability

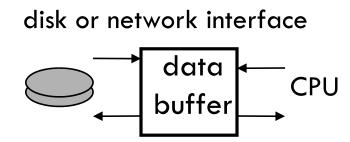


## Multi-Ported SRAM

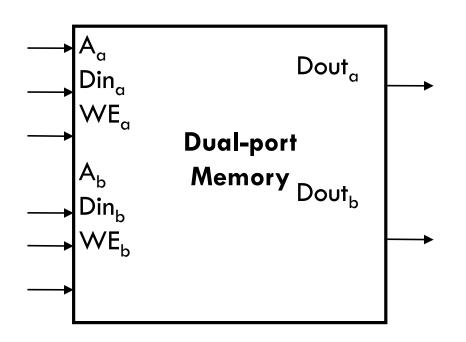
## Multi-Ported Memory

#### Motivation:

- Consider CPU core register file:
  - 1 read or write per cycle limits processor performance.
  - Complicates pipelining. Difficult for different instructions to simultaneously read or write regfile.
  - Single-issue pipelined CPUs usually needs 2 read ports and 1 write port (2R/1W).
  - Superscalar processors have more (e.g. 6R/3W)
  - I/O data buffering:

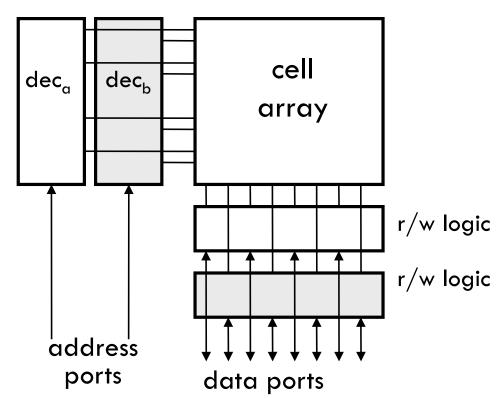


 dual-porting allows both sides to simultaneously access memory at full bandwidth.

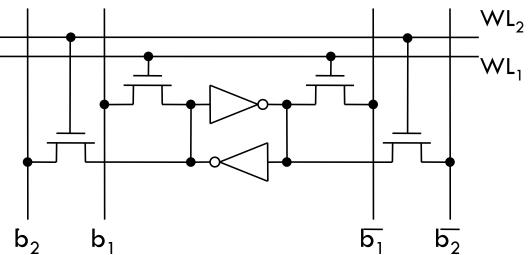


## **Dual-Ported Memory Internals**

 Add decoder, another set of read/write logic, bits lines, word lines:



• Example cell: SRAM



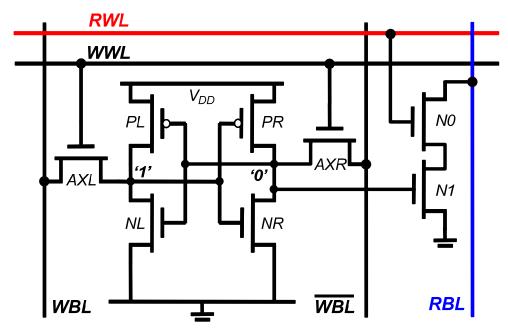
- Repeat everything but cross-coupled inverters.
- This scheme extends up to a couple more ports, then need to add additional transistors.

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## 1R/1W 8T SRAM

#### 8-T SRAM



- Dual-port read/write capability
- Single-cycle read and write, timed appropriately
- Often found in register files, first level (L1) of cache

## True or False

www.yellkey.com/could

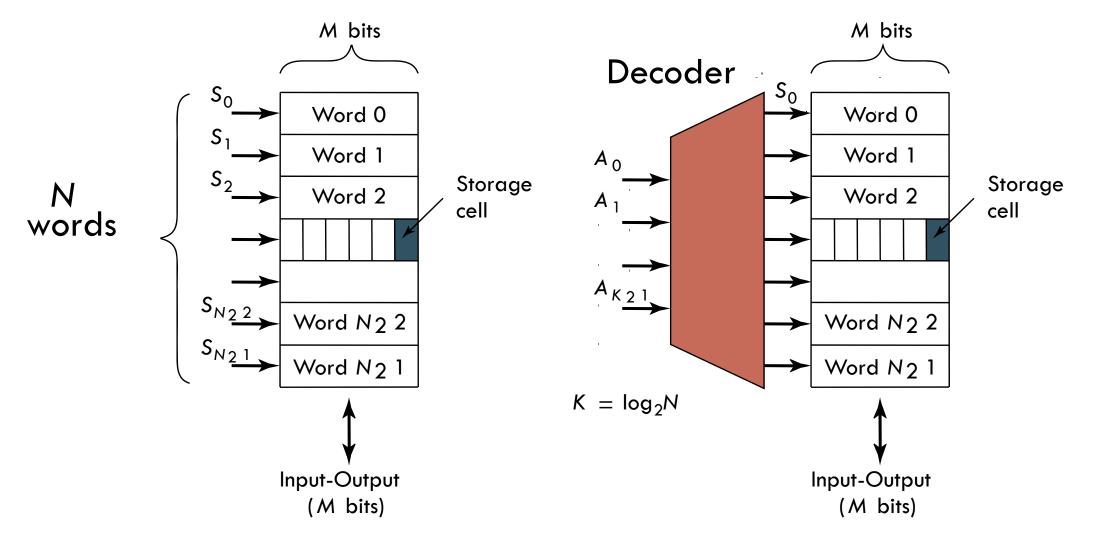
1	F	F	F
2	F	F	T
3	F	Т	F
4	F	Т	T
5	Т	F	F
6	Т	F	T
7	Т	T	F
8	T	Т	T

- 1. Transistor leakage doesn't affect SRAM read speed
- 2. One should write into an SRAM cell by pulling BL high
- 3. One can only write into a part of a selected WL



# Memory Decoders

#### **Decoders**



Intuitive architecture for N x M memory
Too many select signals:
N words = N select signals

Decoder reduces the number of select signals  $K = \log_2 N$ 

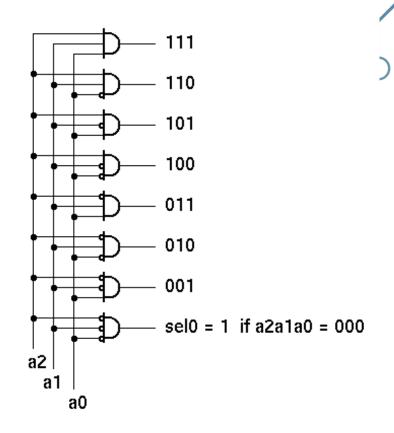
#### Row Decoders



#### (N)AND Decoder

$$WL_0 = \overline{A_0}\overline{A_1}\overline{A_2}\overline{A_3}\overline{A_4}\overline{A_5}\overline{A_6}\overline{A_7}\overline{A_8}\overline{A_9}$$

$$WL_{511} = A_0A_1A_2A_3A_4A_5A_6A_7A_8\overline{A_9}$$



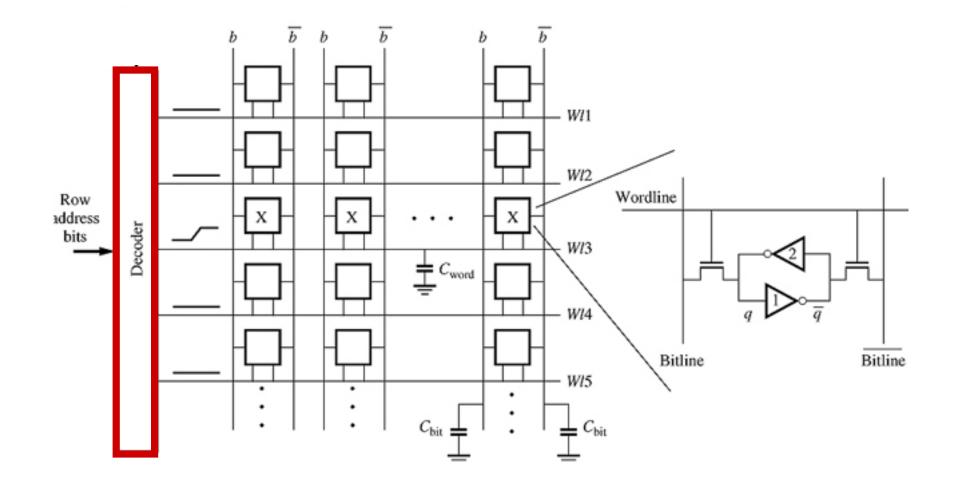
#### **NOR Decoder**

$$WL_0 = A_0 + A_1 + A_2 + A_3 + A_4 + A_5 + A_6 + A_7 + A_8 + A_9$$

$$WL_{511} = \overline{\overline{A_0} + \overline{A_1} + \overline{A_2} + \overline{A_3} + \overline{A_4} + \overline{A_5} + \overline{A_6} + \overline{A_7} + \overline{A_8} + A_9}$$

## Decoder Design Example

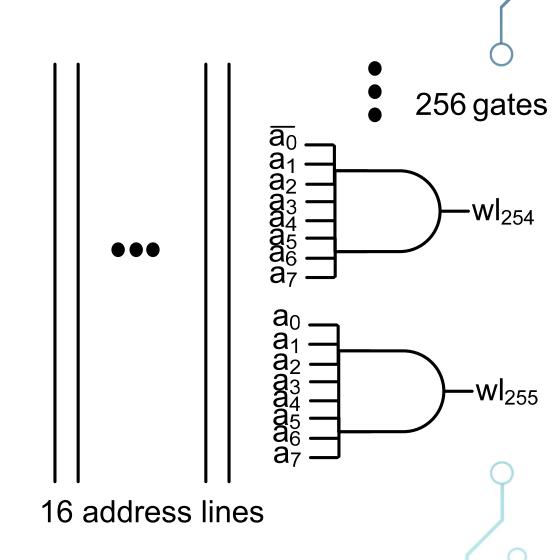
• Look at decoder for 256x256 memory block (8KBytes)



### Possible Decoder

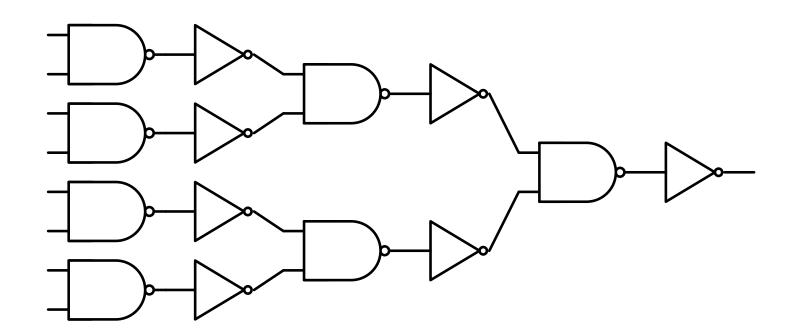
- 256 8-input AND gates
  - Each built out of a tree of NAND gates and inverters

- Need to drive a lot of capacitance (SRAM cells)
  - What's the best way to do this?



## Possible AND8

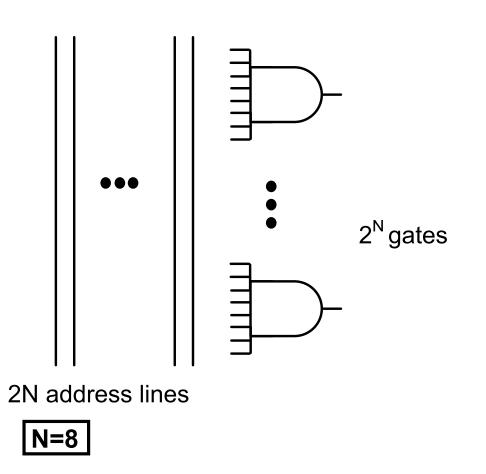
- Build 8-input NAND gate using 2-input gates and inverters
- Is this the best we can do?
- Is this better than using fewer NAND4 gates?



## **Problem Setup**

Goal: Build fastest possible decoder with static CMOS logic

- What we know
  - Basically need 256 AND gates, each one of them drives one word line



## Problem Setup (1)

- Each wordline has 256 cells connected to it
- $C_{WL} = 256*C_{cell} + C_{wire}$ 
  - Ignore wire for now
- Assume that decoder input capacitance is  $C_{address} = 4 C_{cell}$

## Problem Setup (2)

- Each address bit drives  $2^8/2$  AND gates
  - A0 drives  $\frac{1}{2}$  of the gates, A0\_b the other  $\frac{1}{2}$  of the gates

Total fanout on each address wire is:

$$F = \Pi B \frac{C_{load}}{C_{in}} = 128 \frac{\left(256C_{cell}\right)}{4C_{cell}} = 2^{7} \frac{\left(2^{8}C_{cell}\right)}{2^{2}C_{cell}} = 2^{13}$$

#### **Decoder Fan-Out**

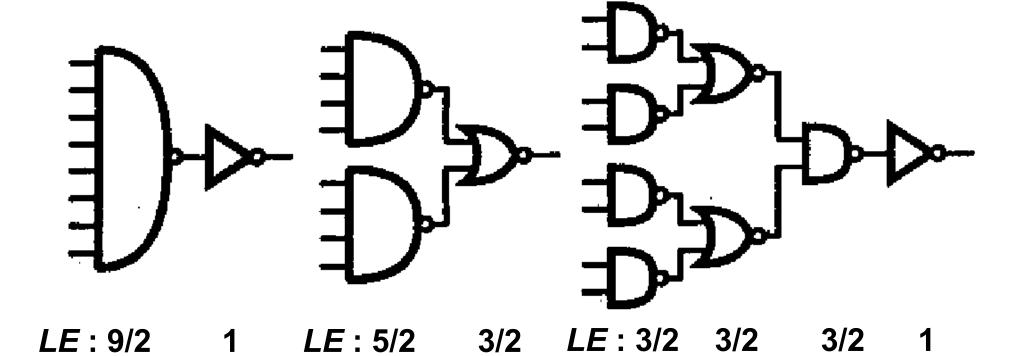
• F of  $2^{13}$  means that we will want to use more than  $\log_4(2^{13}) = 6.5$  stages to implement the AND8

- Need many stages anyways
  - So what is the best way to implement the AND gate?
  - Will see next that it's the one with the most stages and least complicated gates

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## 8-Input AND



 $\Pi$ *LE* = 27/8

P = 2 + 2

 $\Pi$ *LE* = 15/4

P = 4

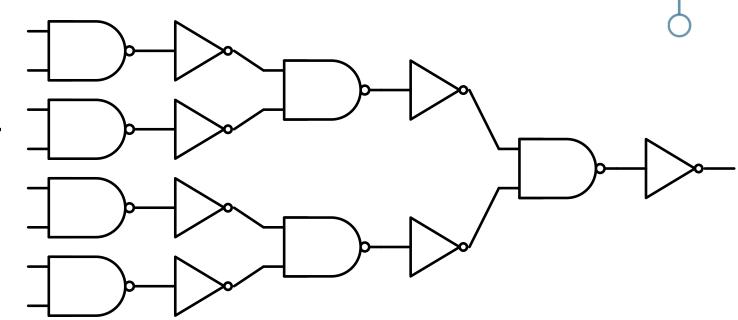
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 $\Pi$ *LE* = 9/2

P = 8 + 1

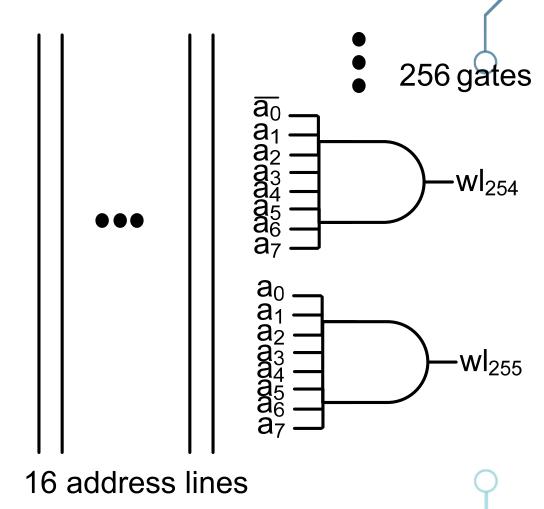
## 8-Input AND

- Using 2-input NAND gates
  - 8-input gate takes 6 stages
- Total LE is  $(3/2)^3 \approx 3.4$
- So PE is  $3.4*2^{13}$  optimal N of ~7.4

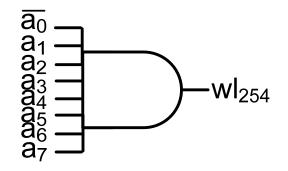


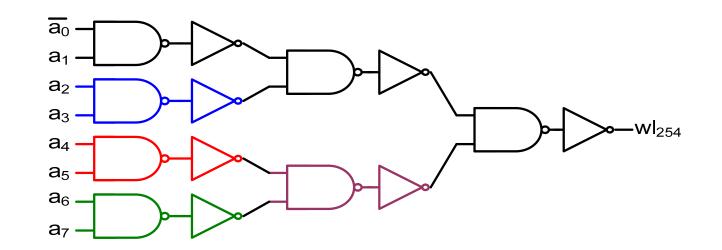
## Decoder So Far

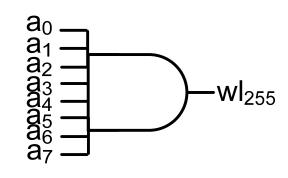
- 256 8-input AND gates
  - Each built out of tree of NAND gates and inverters
- Issue:
  - Every address line has
     to drive 128 gates (and wire) right away
  - Forces us to add buffers just to drive address inputs

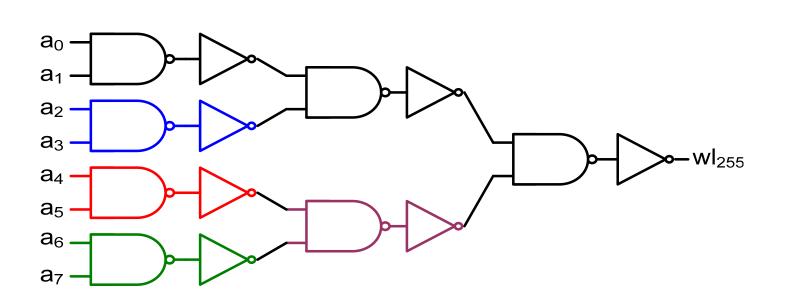


## Look Inside Each AND8 Gate









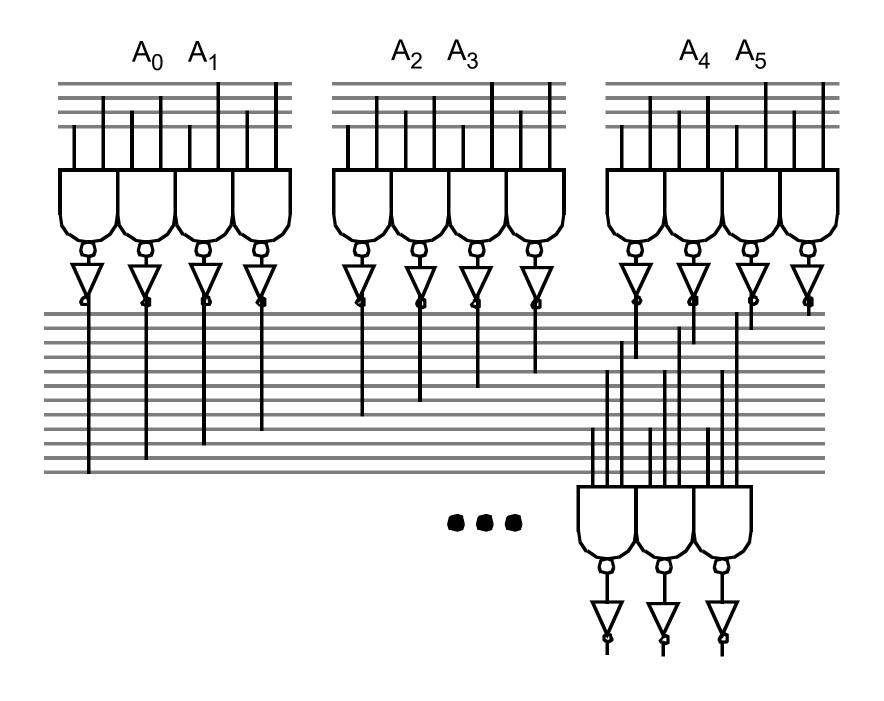
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#### **Predecoders**

- Use a single gate for each of the shared terms
  - E.g., from  $A_0$ ,  $\overline{A_0}$ ,  $A_1$ , and  $\overline{A_1}$ , generate four signals:  $A_0A_1$ ,  $\overline{A_0}A_1$ ,  $A_0\overline{A_1}$ ,  $\overline{A_0}\overline{A_1}$

- In other words, we are decoding smaller groups of address bits first
  - And using the "predecoded" outputs to do the rest of the decoding

## Predecoder and Decoder

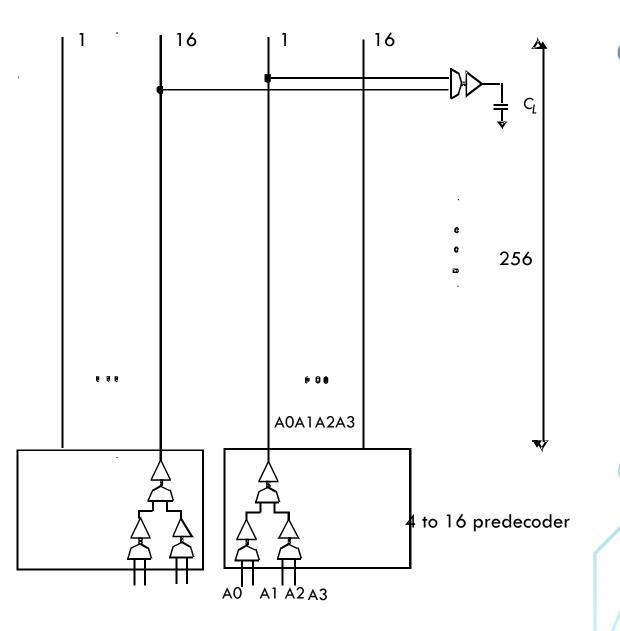


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## Predecode Options

- Larger predecode usually better:
- More stages before the long wires
  - Decreases their effect on the circuit
- Fewer number of long wires switches
  - Lower power
- Easier to fit 2-input gate into cell pitch



## Administrivia

- Projects
  - Checkpoints 2 are this Friday
- Homework 9 due in a week

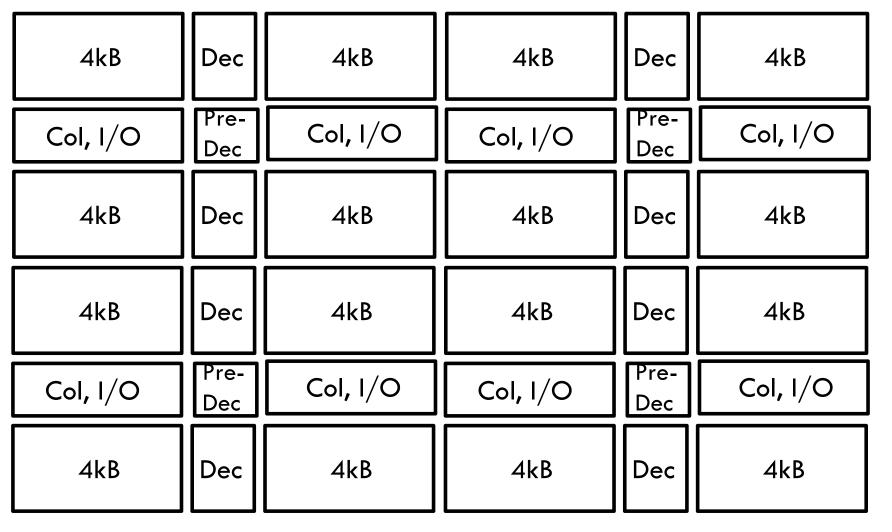


# **Building Larger Arrays**

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## **Building Larger Custom Arrays**



- Each subarray is 2-8kB
- Hierarchical decoding
- Peripheral overhead is 30-50%
- Delay is wire dominated
- Scratchpads, caches, TLBs

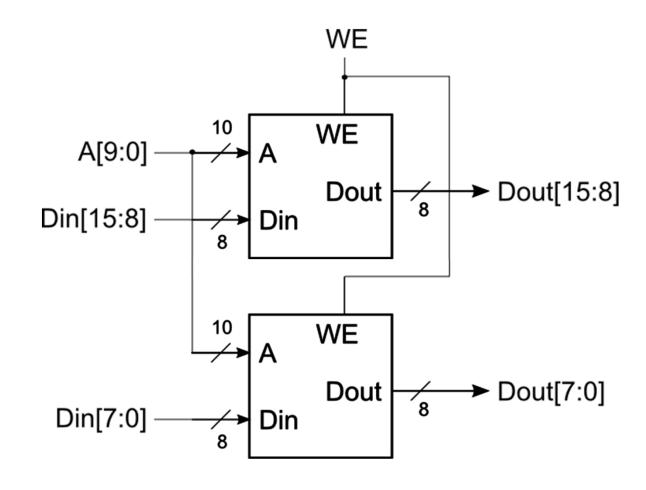
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## Cascading Memory-Blocks

How to make larger memory blocks out of smaller ones.

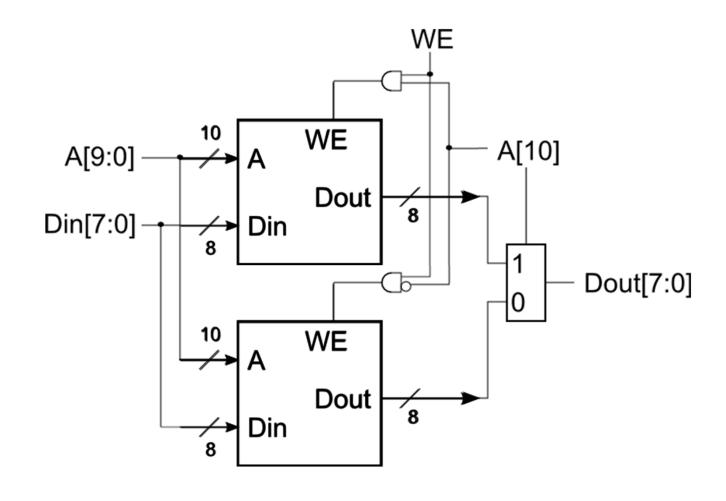
Increasing the width. Example: given 1Kx8, want 1Kx16



## Cascading Memory-Blocks

How to make larger memory blocks out of smaller ones.

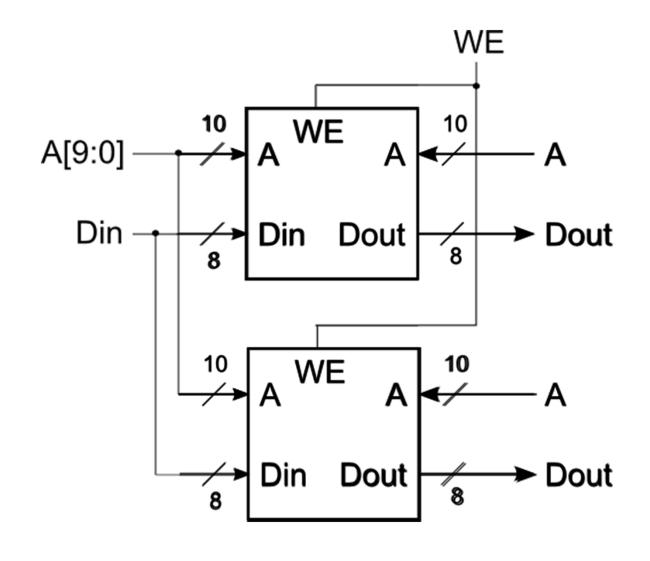
Increasing the depth. Example: given 1Kx8, want 2Kx8



## Adding Ports to Primitive Memory Blocks

Adding a read port to a simple dual port (SDP) memory.

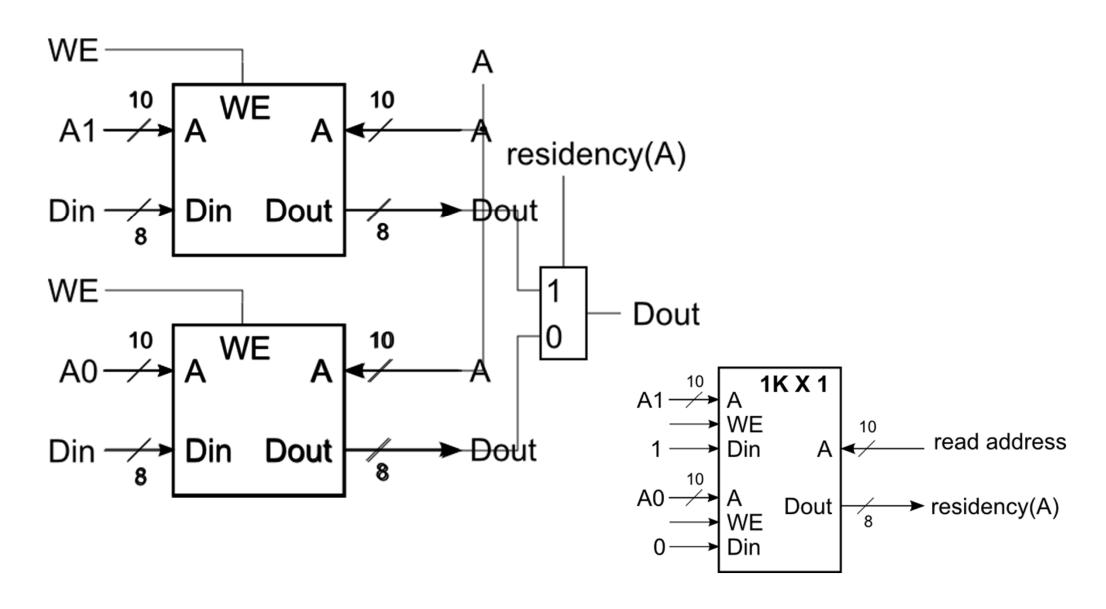
Example: given 1Kx8 SDP, want 1 write & 2 read ports.



## Adding Ports to Primitive Memory Blocks

How to add a write port to a simple dual port memory.

Example: given 1Kx8 SDP, want 1 read & 2 write ports.



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# Caches

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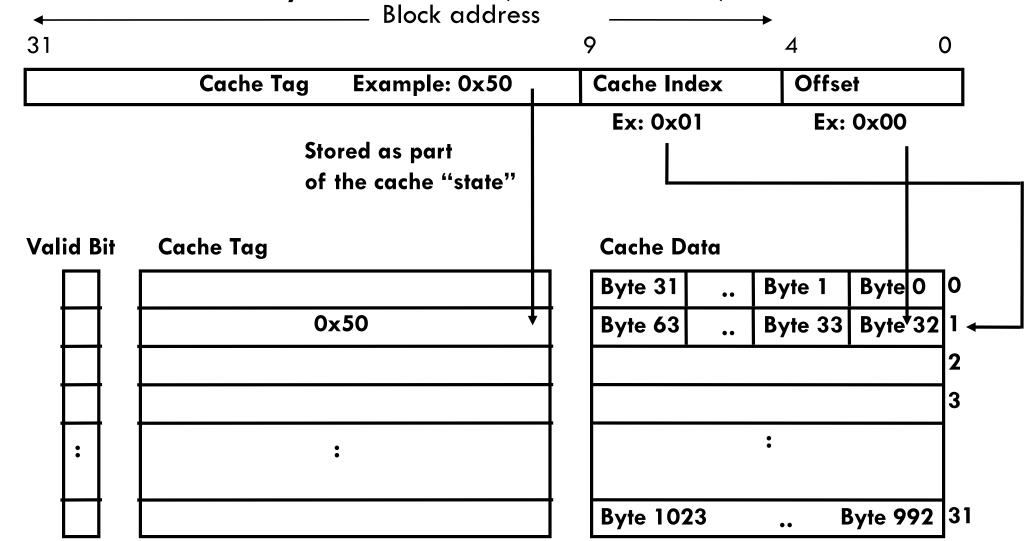
### Caches (Review from 61C)

- Two Different Types of Locality:
  - Temporal locality (Locality in time): If an item is referenced, it tends to be referenced again soon.
  - Spatial locality (Locality in space): If an item is referenced, items whose addresses are close by tend to be referenced soon.
- By taking advantage of the principle of locality:
  - Present the user with as much memory as is available in the cheapest technology.
  - Provide access at the speed offered by the fastest technology.
- DRAM is slow but cheap and dense:
  - Good choice for presenting the user with a BIG memory system
- SRAM is fast but expensive and not as dense:
  - Good choice for providing the user FAST access time.

#### Example: 1 KB Direct Mapped Cache with 32 B Blocks

#### For a 2<sup>N</sup>-byte cache:

- The uppermost (32 N) bits are always the Cache Tag
- The lowest M bits are the byte-select offset (Block Size =  $2^{M}$ )

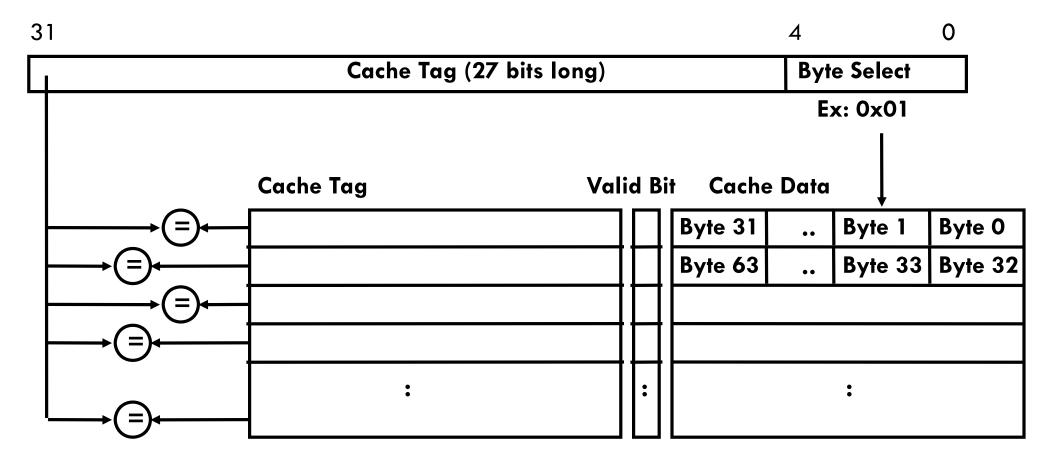


#### Fully Associative Cache

#### **Fully Associative Cache**

- Ignore cache Index for now
- Compare the Cache Tags of all cache entries in parallel (expensive...)\_
- Example: Block Size = 32 B blocks, we need N 27-bit comparators

By definition: Conflict Miss = 0 for a fully associative cache



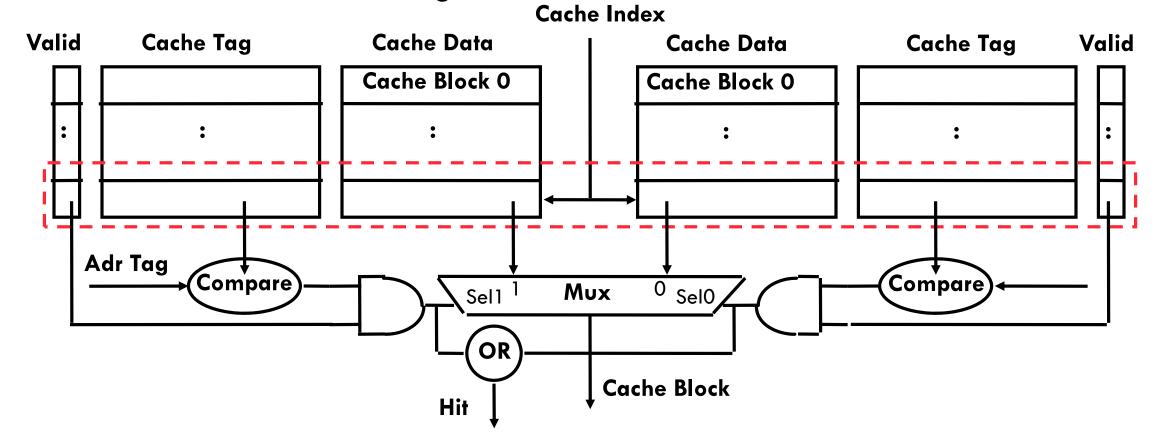
### Set Associative Cache

#### N-way set associative: N entries for each Cache Index

N direct mapped caches operates in parallel

Example: Two-way set associative cache

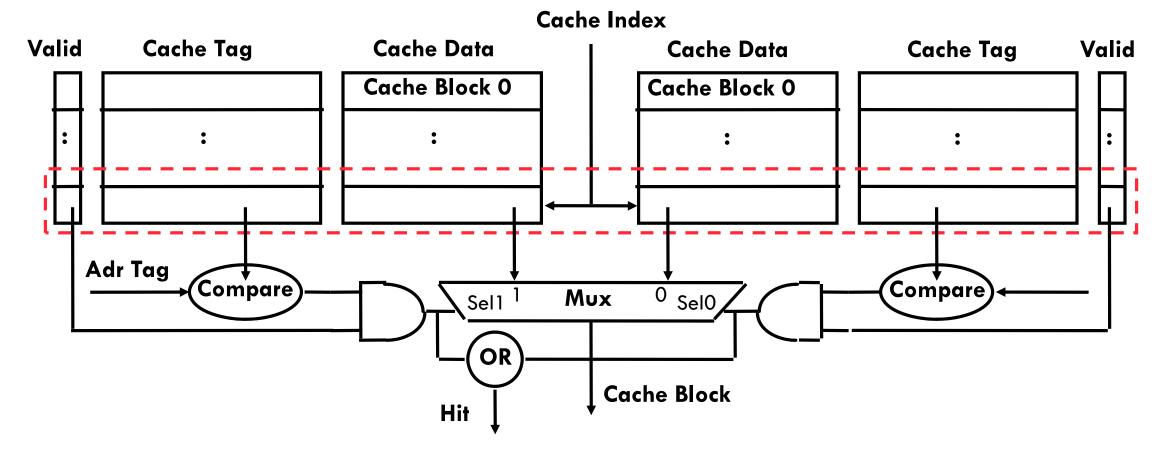
- Cache Index selects a "set" from the cache
- The two tags in the set are compared to the input in parallel
- Data is selected based on the tag result



### Disadvantage of Set Associative Cache

N-way Set Associative Cache versus Direct Mapped Cache:

- N comparators vs. 1
- Extra MUX delay for the data
- Data comes AFTER Hit/Miss decision and set selection
   In a direct mapped cache, Cache Block is available BEFORE Hit/Miss:
  - Possible to assume a hit and continue. Recover later if miss.



### **Block Replacement Policy**

- Direct-Mapped Cache
  - index completely specifies position which position a block can go in on a miss
- N-Way Set Assoc
  - index specifies a set, but block can occupy any position within the set on a miss
- Fully Associative
  - block can be written into any position
- Question: if we have the choice, where should we write an incoming block?
  - If there's a valid bit off, write new block into first invalid.
  - If all are valid, pick a replacement policy
    - rule for which block gets "cached out" on a miss.

## Block Replacement Policy: LRU

- LRU (Least Recently Used)
  - Idea: cache out block which has been accessed (read or write) least recently
  - Pro: temporal locality 
     recent past use implies likely future use: in fact, this is a very effective policy
  - Con: with 2-way set assoc, easy to keep track (one LRU bit); with 4-way or greater, requires more complicated hardware and more time to keep track of this

### Summary

- ullet SRAM and regfile cells can have multiple R/W ports
- Memory decoding is done hierarchically
  - Wire-limited in large arrays
- Multiple cache levels make memory appear both fast and big
- Direct mapped and set-associative cache

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